

cooling the crystalline semiconductor film by applying a second cooling gas after the gettering.

In contrast, Yamazaki '667 in cols. 12-13 and Fig. 18 (cited by the Examiner in the Office Action) states that the crystal silicon film is cooled but does not disclose the specific steps of intentionally cooling the film by applying a first and then a second cooling gas, as in the claims of the present application.

Accordingly, Yamazaki '667 does not disclose the claimed invention, and the claims are patentable thereover. Therefore, it is respectfully requested that this rejection be withdrawn.

#### Claim Rejections - 35 USC §103

The Examiner also rejects Claims 29-30, 33-35 and 37-43 under 35 USC §103(a) as being unpatentable over Yamazaki '667 in view of Udea et al. (US 6,337,259). This rejection is also respectfully traversed.

For at least the reasons discussed above, these claims are also not disclosed by Yamazaki '667.

The Examiner also cites Udea. Applicant, however, could not find any discussion of cooling in the reference. The Examiner cites the abstract, col. 6 lns. 10-30 and col. 5 lns. 25-33 of Udea in support of his rejection. However, each of these sections appears to discuss gettering, not cooling, and using nitrogen and helium during gettering, not cooling. Hence, Udea also does not disclose or suggest the claimed invention, and even if it were combined with Yamazaki '667 (which Applicants do not admit would be proper), the combination still fails to disclose or suggest the claimed invention.